PATENT APPLICATION

Navy Case No. 79,849

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.'

Listing of Claims

Claims 72-74, 85-99, 101 and 102 are all cancelled.

- 54. (allowed) A detector for detecting a photon, comprising:
 - a substrate,
 - a photon absorber disposed upon said substrate,
- a thermoelectric sensor, disposed upon said substrate and thermally coupled with said photon absorber, and
 - a heat sink disposed upon said substrate, thermally coupled to the thermoelectric sensor,

for absorbing a photon and generating a voltage differential across said sensor between said absorber and said heat sink in response to said photon absorption.

- 55. (allowed) The detector of claim 54, further comprising means to measure said voltage differential.
- 56. (allowed) The detector of claim 54, wherein said substrate comprises a dielectric material.

PATENT APPLICATION

Navy Case No. 79,849

57. (currently amended) The detector of claim 54, wherein responsive to arrival of a said

photon,

said absorber is heated,

so that heat in said absorber is transferred to said sensor and further transferred to said

heat sink.

58. (currently amended) The detector of claim 54, wherein said heat is transferred from said

absorber to said heat sink faster than heat is transferred from said absorber to said substrate.

59. (currently amended) The detector of claim 58, wherein the time for said heat to be

transferred from said absorber to said heat sink is about ten times less than the time for heat to be

transferred from said absorber to said substrate.

60. (allowed) The detector of claim 55, further comprising superconducting leads for measuring

said voltage differential.

61. (allowed) The detector of claim 60, further comprising an input coil of a flux transformer

electrically connected to said superconducting leads.

62. (allowed) The detector of claim 60, further comprising an input coil of a flux transformer of

a superconducting quantum interference device circuit electrically connected to said

superconducting leads.

5

PATENT APPLICATION

Navy Case No. 79,849

63. (allowed) The detector of claim 54, wherein the absorber and the heat sink have the same heat capacity.

- 64. (allowed) The detector of claim 63, wherein the absorber and the heat sink are alike in material and geometry.
- 65. (allowed) The detector of claim 54, wherein said thermoelectric sensor comprises a thin film disposed upon said substrate.
- 66. (allowed) The detector of claim 54, wherein said thermoelectric sensor comprises a material with isotropic thermoelectric properties.
- 67. (allowed) The detector of claim 65, wherein said thin film comprises gold with impurities.
- 68. (allowed) The detector of claim 65, wherein said thin film comprises gold with iron impurities between about 10 ppm and 100 ppm.
- 69. (allowed) The detector of claim 65, wherein said thin film comprises a metal with a Seebeck coefficient of at least about 10 μ V/K at an operating temperature of said detector.

PATENT APPLICATION

Navy Case No. 79,849

70. (allowed) The detector of claim 65, wherein said thin film comprises a metal with a Seebeck coefficient of between about 10 μ V/K and about 80 μ V/K at an operating temperature of said detector.

- 71. (allowed) The detector of claim 65, wherein said thin film comprises lanthanum cerium hexaboride.
- 75. (allowed) The detector of claim 54, further comprising a superconducting element electrically coupled to the heat sink and the photon absorber.
- 76. (allowed) The detector of claim 54, further comprising said sensor connected between said absorber and said heat sink.
- 77. (allowed) The detector of claim 54, further comprising niobium electric leads attached to said heat sink and to said absorber for measuring said voltage differential.
- 78. (allowed) The detector of claim 54, wherein said sensor has a resistance R which is less than r_0L_0/T^2A_{abs} , where r_0 is the Kapitza resistance constant between the absorber and the substrate, L_0 is the Lorenz number, T is the operating temperature of the detector, and A_{abs} , is the cross se ctional area of the absorber.

PATENT APPLICATION

Navy Case No. 79,849

79. (allowed) The detector of claim 78, wherein said r_0 is about 20 K^4 cm 2 / W and said L_0 is

about 25 nW- Ω/K^2 .

80. (allowed) A photon detector comprising:

a thin dielectric wafer having a photon absorber disposed on the edge of said wafer,

a thermoelectric sensor disposed on said wafer, and

a heat sink disposed on said wafer,

wherein said thermoelectric sensor is thermally coupled with said photon absorber, said

heat sink is thermally coupled to said thermoelectric sensor,

for absorbing a photon and generating a potential across said sensor, whereby there is a

voltage differential between said absorber and said heat sink in response to said photon

absorption.

81. (allowed) The photon detector of claim 80, wherein

said heat sink and said thermoelectric sensor are disposed on the edge of said wafer

82. (allowed) The photon detector of claim 81, further comprising a voltage differential

measuring means disposed upon a face of said wafer.

83. (allowed) The photon detector of claim 82, wherein said voltage differential measuring

means comprises a SQUID array amplifier.

8

PATENT APPLICATION

Navy Case No. 79,849

84. (allowed) The photon detector of claim 83, wherein said voltage differential measuring means comprises semiconductor electronics.

100. (allowed) A photon detector as in claim 65, wherein said thin film comprises CeNiSn.